TOSHIBA PHOTO-INTERRUPTER INFRARED LED + PHOTOTRANSISTOR

TLP810

MOTOR ROTATION AND IRIS DETECTION FOR CAMERAS

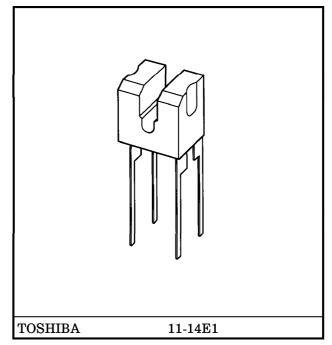
TRACK DETECTION IN MICRO FLOPPY DISK DRIVE

• Very small package

• High resolution: Slit width = 0.4 mm

• Gap : 1 mm

• Can be mounted directly on PCB using the stand off of lead.



Weight: 0.07 g (typ.)

MAXIMUM RATINGS ($Ta = 25^{\circ}C$)

CHARACTERISTIC		SYMBOL	RATING	UNIT	
LED	Forward Current	$I_{\mathbf{F}}$	50	mA	
	Forward Current Derating (Ta > 25°C)	I _F /°C	-0.67	mA/°C	
	Reverse Voltage	$v_{ m R}$	5	V	
DETECTOR	Collector-Emitter Voltage	VCEO	35	V	
	Emitter Collector Voltage	v_{ECO}	5	V	
	Collector Current	$I_{\mathbb{C}}$	20	mA	
	Collector Power Dissipation	PC	75	mW	
	Collector Power Dissipation $(Ta > 25^{\circ}C)$	ΔP _C /°C	-1	mW/°C	
Operating Temperature Range		$T_{ m opr}$	-25~85	°C	
Storage Temperature Range		$\mathrm{T_{stg}}$	-40~100	$^{\circ}\mathrm{C}$	

OPTICAL AND ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	Min	Тур.	Max	UNIT
LED	Forward Voltage	$V_{\mathbf{F}}$	$I_{ m F}=10{ m mA}$	1.00	1.15	1.30	V
	Reverse Current	$I_{\mathbf{R}}$	$V_{R} = 5 V$	_		10	μ A
	Capacitance	C_{T}	V = 0, f = 1 MHz	-	30	_	pF
DETECTOR	Dark Current	I _D (I _{CEO})	$V_{ m CE} = 20 m V, I_{ m F} = 0$	1	1	100	nA
	Capacitance	C_{T}	$V=0, \ f=1 \ \mathrm{MHz}$	1	13	1	pF
COUPLED	Current Transfer Ratio	I_C/I_F	$ m V_{CE} = 0.6 V, I_{F} = 5 mA$	5	_	30	%
	Collector-Emitter Saturation Voltage	V _{CE} (sat)	$I_{\mathrm{F}}=8\mathrm{mA},~I_{\mathrm{C}}=0.1\mathrm{mA}$	_	0.1	0.4	V
	Rise Time	$t_{\mathbf{r}}$	$V_{CC} = 5 \text{ V}, I_{C} = 0.2 \text{ mA},$		50		
	Fall Time	t_f	$R_{\rm L} = 1 \mathrm{k} \Omega$		50	_	μ s

PRECAUTIONS

The following points must be borne in mind.

1. Soldering temperature: 260°C max

Soldering time: 5 s max

(Soldering must be performed 1.5 mm under the stopper.)

2. Ensure that no residual flux or chemicals adhere to the light-emitting and light-receiving surfaces.

ENVIRONMENT

- O The device should not be exposed to corrosive gases, such as hydrogen sulfide gas and a sea breeze.
- O The device should not be exposed to dust.
- The device should not be exposed to direct sunlight.
 In essence, the device should not be subjected to any load which may result in deformation or performance deterioration.

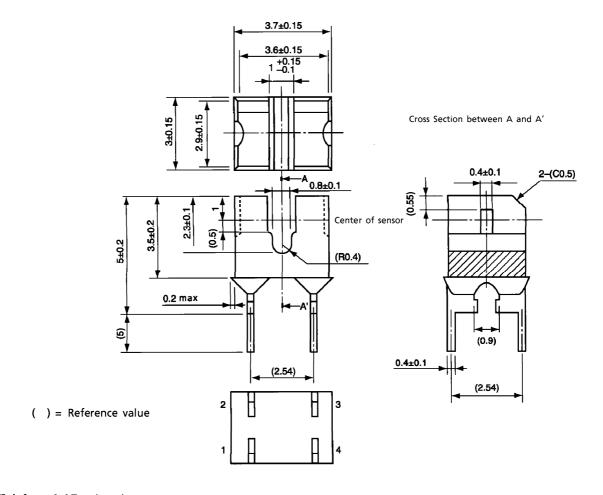
CIRCUIT DESIGN

• Conversion efficiency falls over time due to the current which flows in the infrared LED. When designing a circuit, take into account this change in conversion efficiency over time. The ratio of fluctuation in conversion efficiency to fluctuation in infrared LED optical output is 1:1.

$$\frac{I_{C}/I_{F}(t)}{I_{C}/I_{F}(0)} = \frac{P_{O}(t)}{P_{O}(0)}$$

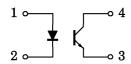
PACKAGE DIMENSIONS 11-14E1

Unit: mm

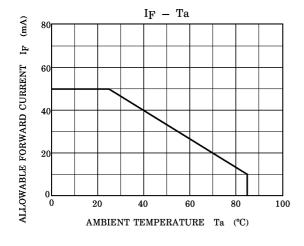


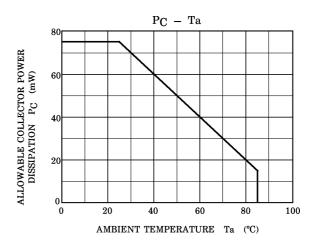
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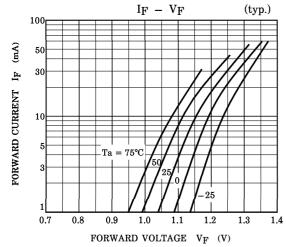
PIN CONNECTION

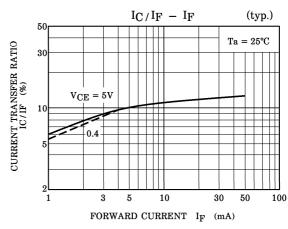


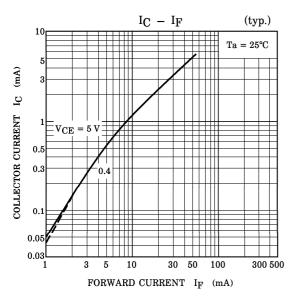
- 1. Anode
- 2. Cathode
- 3. Emitter
- 4. Collector

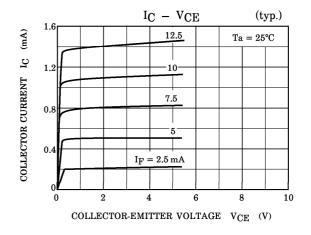


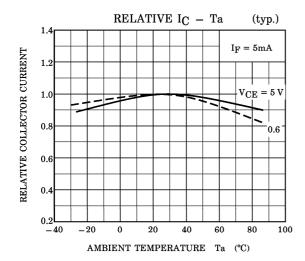


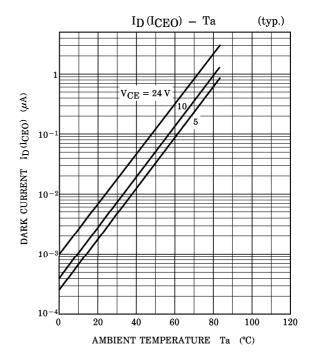


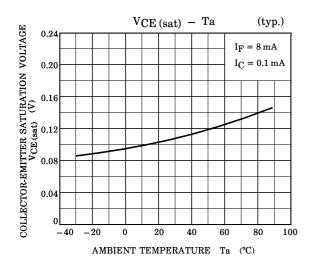


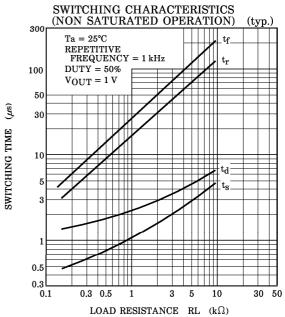


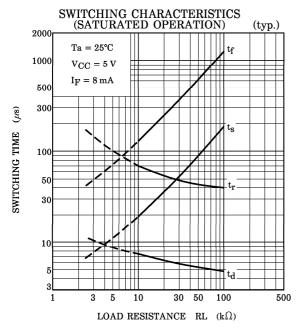


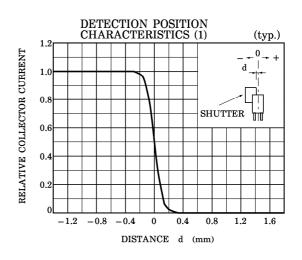


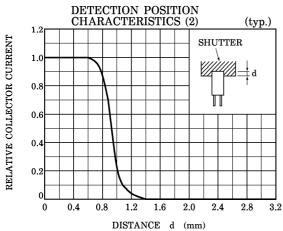


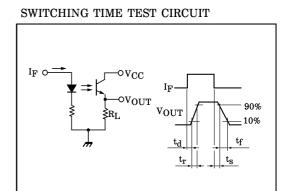












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